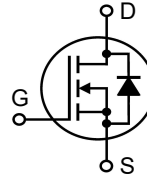


# X4-Class Power MOSFET™

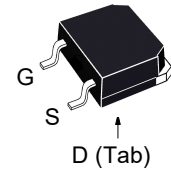
## IXTT220N20X4HV

$$\begin{aligned} V_{DSS} &= 200V \\ I_{D25} &= 220A \\ R_{DS(on)} &\leq 5.5m\Omega \end{aligned}$$

N-Channel Enhancement Mode  
Avalanche Rated



TO-268HV  
(IXTT..HV)



G = Gate      D = Drain  
S = Source    Tab = Drain

| Symbol       | Test Conditions                                                          | Maximum Ratings |                  |
|--------------|--------------------------------------------------------------------------|-----------------|------------------|
| $V_{DSS}$    | $T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$                          | 200             | V                |
| $V_{DGR}$    | $T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$ , $R_{GS} = 1M\Omega$    | 200             | V                |
| $V_{GSS}$    | Continuous                                                               | $\pm 20$        | V                |
| $V_{GSM}$    | Transient                                                                | $\pm 30$        | V                |
| $I_{D25}$    | $T_C = 25^\circ\text{C}$                                                 | 220             | A                |
| $I_{L(RMS)}$ | External Lead Current Limit                                              | 160             | A                |
| $I_{DM}$     | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$               | 400             | A                |
| $I_A$        | $T_C = 25^\circ\text{C}$                                                 | 110             | A                |
| $E_{AS}$     | $T_C = 25^\circ\text{C}$                                                 | 900             | mJ               |
| $dv/dt$      | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ | 50              | V/ns             |
| $P_D$        | $T_C = 25^\circ\text{C}$                                                 | 800             | W                |
| $T_J$        |                                                                          | -55 ... +175    | $^\circ\text{C}$ |
| $T_{JM}$     |                                                                          | 175             | $^\circ\text{C}$ |
| $T_{stg}$    |                                                                          | -55 ... +175    | $^\circ\text{C}$ |
| $T_{SOLD}$   | Plastic Body for 10s                                                     | 260             | $^\circ\text{C}$ |
| Weight       |                                                                          | 4               | g                |

### Features

- International Standard Package
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified) | Characteristic Values |      |                      |
|--------------|-----------------------------------------------------------------------------|-----------------------|------|----------------------|
|              |                                                                             | Min.                  | Typ. | Max.                 |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 250\mu A$                                            | 200                   |      | V                    |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$                                        | 2.5                   |      | 4.5 V                |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                                          |                       |      | $\pm 100$ nA         |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 150^\circ\text{C}$             |                       |      | 10 $\mu A$<br>1.5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                         |                       | 4.1  | 5.5 m $\Omega$       |

| Symbol                                        | Test Conditions<br>( $T_J = 25^{\circ}\text{C}$ , Unless Otherwise Specified)                                                                      | Characteristic Values                                |             |                           |
|-----------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------|-------------|---------------------------|
|                                               |                                                                                                                                                    | Min.                                                 | Typ.        | Max                       |
| $g_{fs}$                                      | $V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1                                                                                                | 90                                                   | 150         | S                         |
| $R_{Gi}$                                      | Gate Input Resistance                                                                                                                              |                                                      | 1.6         | $\Omega$                  |
| $C_{iss}$<br>$C_{oss}$<br>$C_{rss}$           | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$                                                                                   |                                                      | 12.3        | nF                        |
|                                               |                                                                                                                                                    |                                                      | 1650        | pF                        |
|                                               |                                                                                                                                                    |                                                      | 5.4         | pF                        |
| <b>Effective Output Capacitance</b>           |                                                                                                                                                    |                                                      |             |                           |
| $C_{o(er)}$<br>$C_{o(tr)}$                    | Energy related<br>Time related                                                                                                                     | $V_{GS} = 0\text{V}$<br>$V_{DS} = 0.8 \cdot V_{DSS}$ | 900<br>3400 | pF<br>pF                  |
| $t_{d(on)}$<br>$t_r$<br>$t_{d(off)}$<br>$t_f$ | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$<br>$R_G = 2\Omega$ (External) |                                                      | 30          | ns                        |
|                                               |                                                                                                                                                    |                                                      | 15          | ns                        |
|                                               |                                                                                                                                                    |                                                      | 87          | ns                        |
|                                               |                                                                                                                                                    |                                                      | 6           | ns                        |
| $Q_{g(on)}$<br>$Q_{gs}$<br>$Q_{gd}$           | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$                                                                   |                                                      | 157         | nC                        |
|                                               |                                                                                                                                                    |                                                      | 50          | nC                        |
|                                               |                                                                                                                                                    |                                                      | 46          | nC                        |
| $R_{thJC}$                                    |                                                                                                                                                    |                                                      |             | 0.19 $^{\circ}\text{C/W}$ |

#### Source-Drain Diode

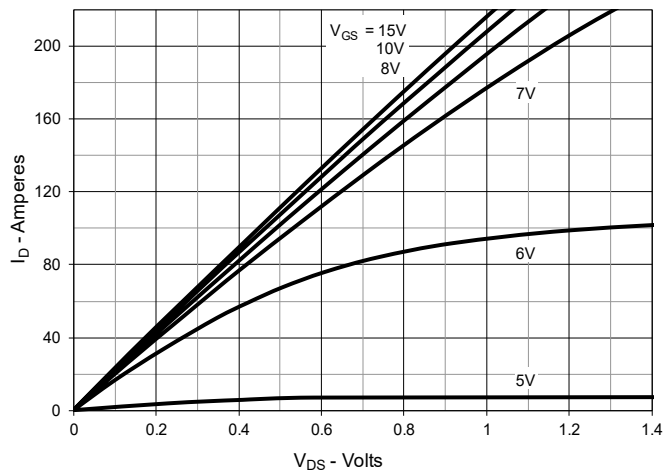
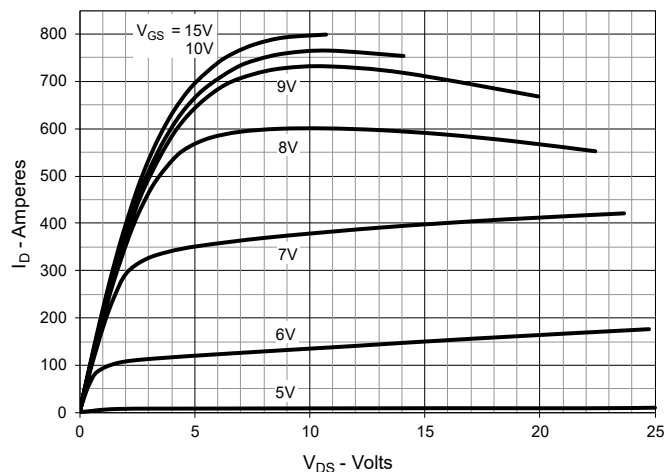
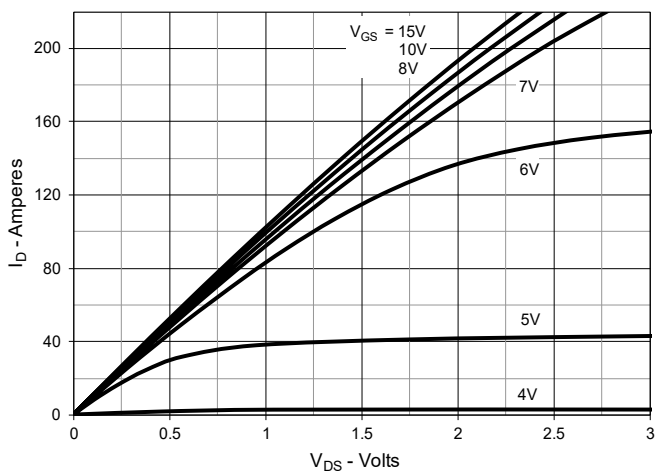
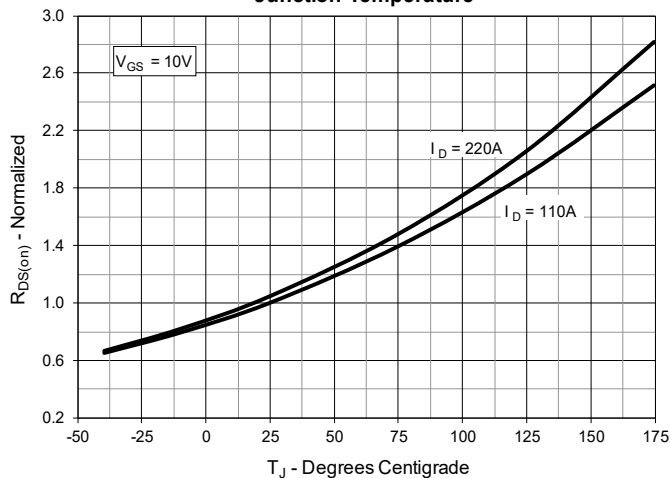
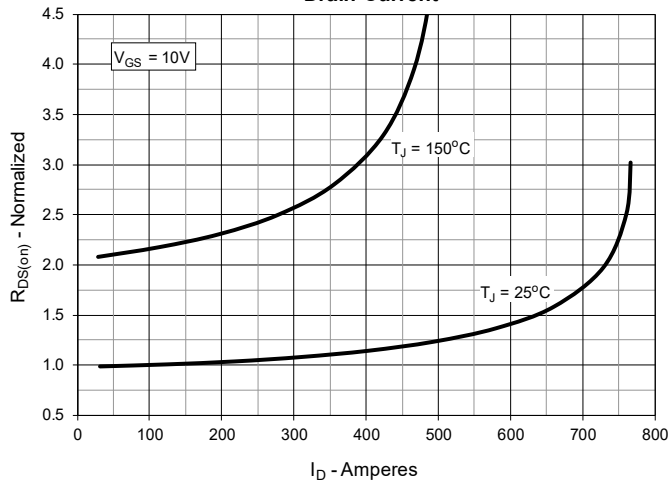
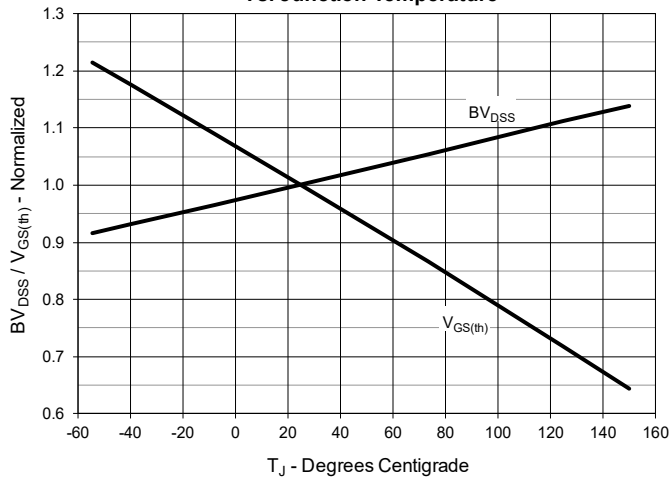
| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)     | Characteristic Values |      |       |
|----------|---------------------------------------------------------------------------------|-----------------------|------|-------|
|          |                                                                                 | Min.                  | Typ. | Max   |
| $I_S$    | $V_{GS} = 0\text{V}$                                                            |                       |      | 220 A |
| $I_{SM}$ | Repetitive, pulse Width Limited by $T_{JM}$                                     |                       |      | 880 A |
| $V_{SD}$ | $I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1                             |                       |      | 1.4 V |
| $t_{rr}$ | $I_F = 110\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}$ |                       | 140  | ns    |
| $Q_{RM}$ |                                                                                 |                       | 770  | nC    |
| $I_{RM}$ |                                                                                 |                       | 11   | A     |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

Littelfuse reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

|           |           |           |           |             |             |             |             |             |             |
|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665   | 6,404,065B1 | 6,683,344   | 6,727,585   | 7,005,734B2 | 7,157,338B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343   | 6,710,405B2 | 6,759,692   | 7,063,975B2 |             |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505   | 6,710,463   | 6,771,478B2 | 7,071,537   |             |

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 110\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 110\text{A}$  Value vs. Drain Current**

**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**


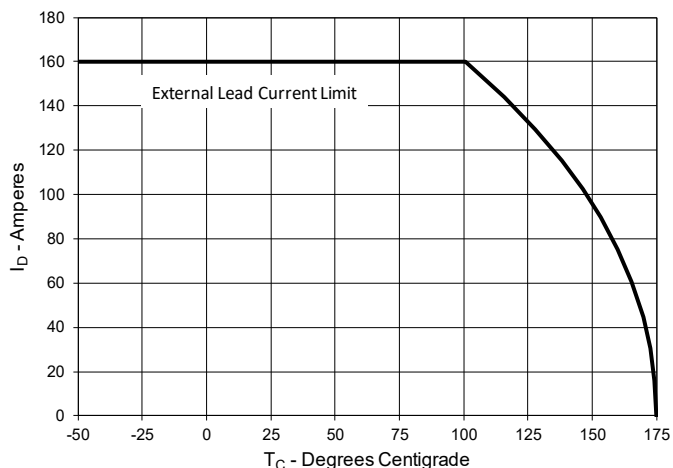
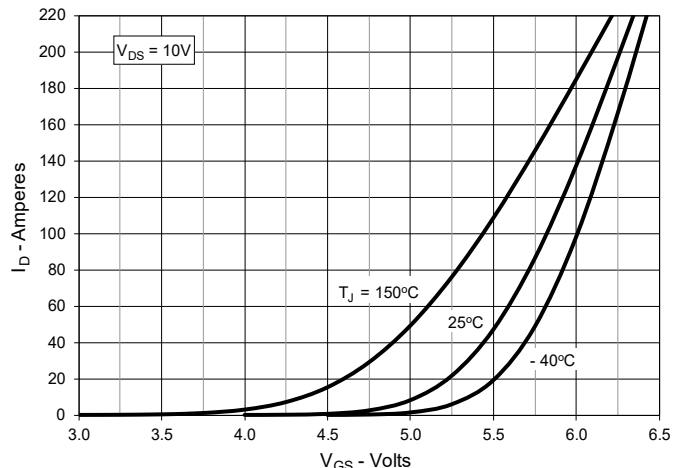
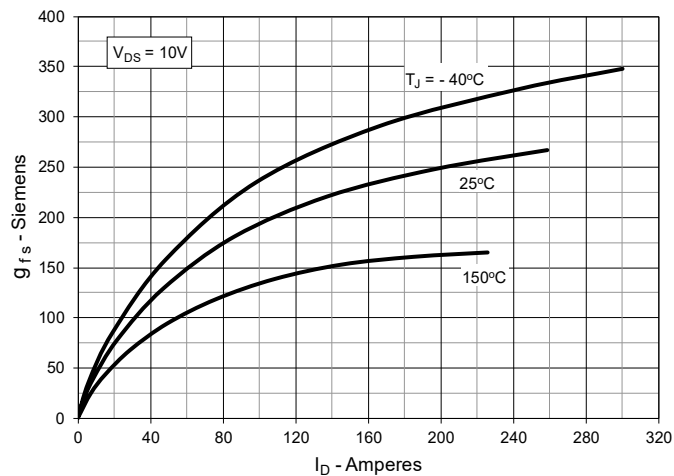
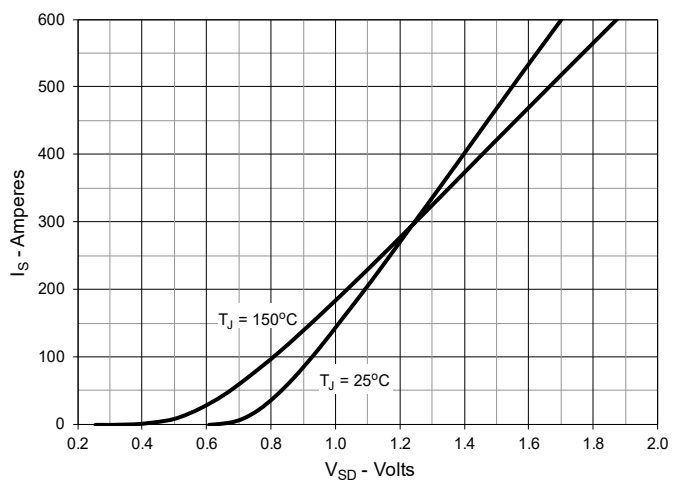
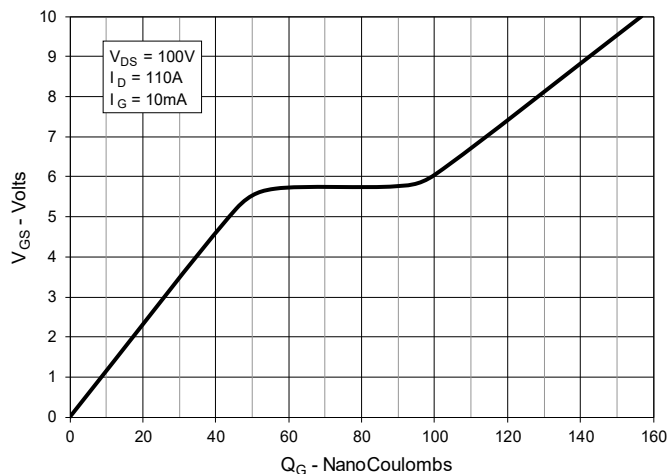
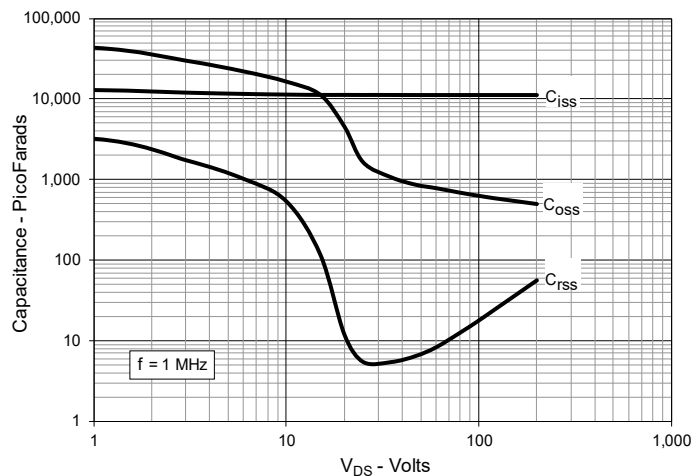
**Fig. 7. Maximum Drain Current vs. Case Temperature**

**Fig. 8. Input Admittance**

**Fig. 9. Transconductance**

**Fig. 10. Forward Voltage Drop of Intrinsic Diode**

**Fig. 11. Gate Charge**

**Fig. 12. Capacitance**


Fig. 13. Output Capacitance Stored Energy

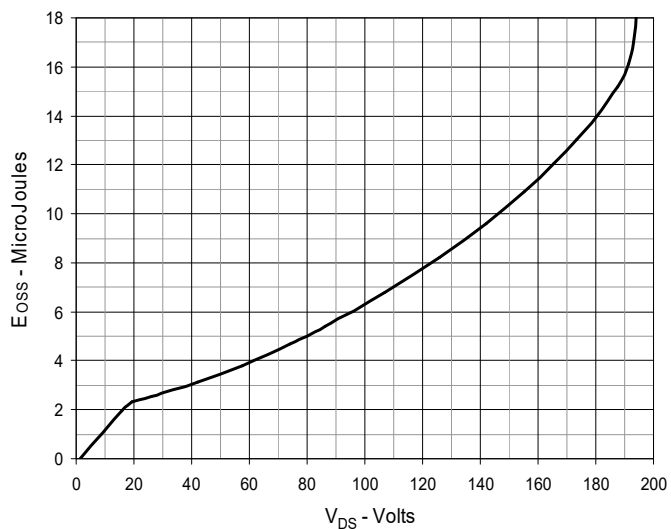


Fig. 14. Forward-Bias Safe Operating Area

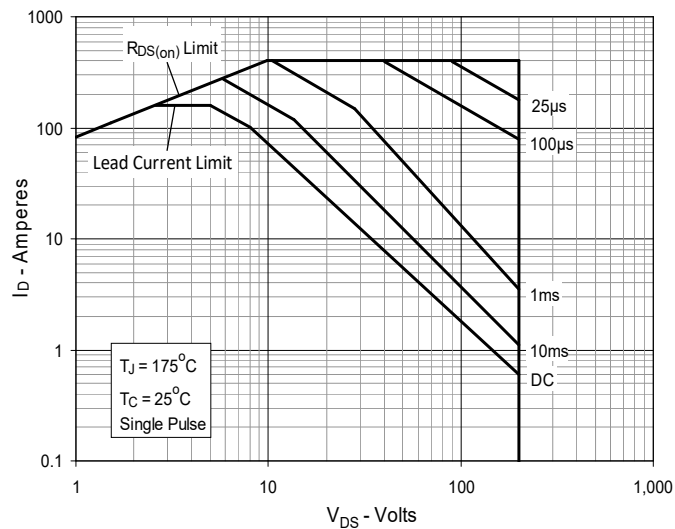
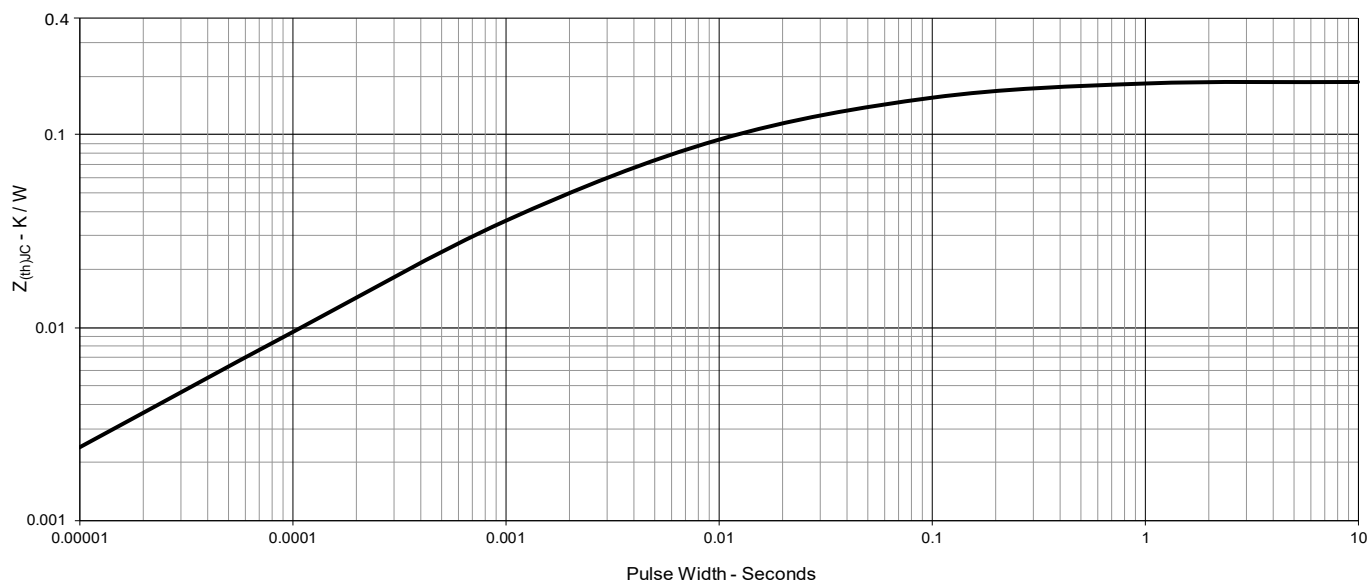
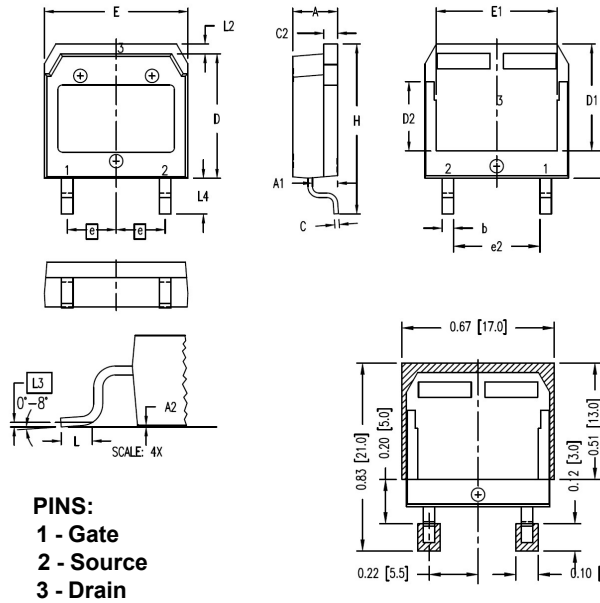


Fig. 15. Maximum Transient Thermal Impedance



**TO-268HV Outline**


| SYM  | INCHES   |      | MILLIMETER |       |
|------|----------|------|------------|-------|
|      | MIN      | MAX  | MIN        | MAX   |
| A    | .193     | .201 | 4.90       | 5.10  |
| A1   | .106     | .114 | 2.70       | 2.90  |
| A2   | .001     | .010 | 0.02       | 0.25  |
| b    | .045     | .057 | 1.15       | 1.45  |
| C    | .016     | .026 | 0.40       | 0.65  |
| C2   | .057     | .063 | 1.45       | 1.60  |
| D    | .543     | .551 | 13.80      | 14.00 |
| D1   | .465     | .476 | 11.80      | 12.10 |
| D2   | .295     | .307 | 7.50       | 7.80  |
| D3   | .114     | .126 | 2.90       | 3.20  |
| E    | .624     | .632 | 15.85      | 16.05 |
| E1   | .524     | .535 | 13.30      | 13.60 |
| e    | .215 BSC |      | 5.45 BSC   |       |
| (e2) | .374     | .386 | 9.50       | 9.80  |
| H    | .736     | .752 | 18.70      | 19.10 |
| L    | .067     | .079 | 1.70       | 2.00  |
| L2   | .039     | .045 | 1.00       | 1.15  |
| L3   | .010 BSC |      | 0.25 BSC   |       |
| L4   | .150     | .161 | 3.80       | 4.10  |

